

## N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$R_{DS(on)}\left(\Omega\right)$	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ.)	
30	0.0030 at $V_{GS} = 10 \text{ V}$	30	36	
	$0.0040$ at $V_{GS} = 4.5 \text{ V}$	27	30	

#### **FEATURES**

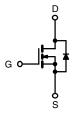
- · Halogen-free available
- Ultra-Low On-Resistance Using High Density TrenchFET® Gen II Power MOSFET Technology



- Q<sub>g</sub> Optimized
- New Low Thermal Resistance PowerPAK<sup>®</sup> Package with Low 1.07 mm Profile
- 100 % R<sub>g</sub> Tested
- 100 % UIS Tested

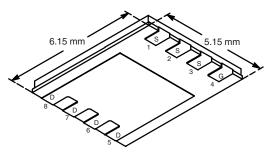
#### **APPLICATIONS**

- Low-Side DC/DC Conversion
  - Notebook
  - Server
  - Workstation



N-Channel MOSFET

#### PowerPAK SO-8



**Bottom View** 

Ordering Information: Si7336ADP-T1-E3 (Lead (Pb)-free)

Si7336ADP-T1-GE3 (Lead (Pb)-free and Halogen-free)

<b>ABSOLUTE MAXIMUM RATINGS</b>	Γ <sub>A</sub> = 25 °C, unles	ss otherwise n	oted		
Parameter		Symbol	Limits	Unit	
Drain-Source Voltage		$V_{DS}$	30	V	
Gate-Source Voltage		$V_{GS}$	± 20	\ \ \	
Continuous Drain Current (T <sub>.I</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 25 °C	- I <sub>D</sub>	30		
Continuous Drain Current (1 j = 150 °C)	T <sub>A</sub> = 70 °C		25		
Pulsed Drain Current (10 μs Pulse Width)		I <sub>DM</sub>	70	Α	
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	4.5		
Avalanche Current	L = 0.1 mH	I <sub>AS</sub> 50			
Maximum Dawar Dissinations	T <sub>A</sub> = 25 °C	$P_{D}$	5.4	W	
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 70 °C	] ' D	3.4		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C	
Soldering Recommendations (Peak Temperature) <sup>b, c</sup>			260		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>a</sup>	t ≤ 10 s	R <sub>thJA</sub>	18	23	°C/W	
Maximum Junction-to-Ambient	Steady State		50	65		
Maximum Junction-to-Case (Drain)	Steady State	R <sub>thJC</sub>	1.0	1.5		

#### Notes

- a. Surface Mounted on 1" x 1" FR4 board.
- b. See Solder Profile ( <a href="http://www.vishay.com/ppg?73257">http://www.vishay.com/ppg?73257</a>). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- c. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

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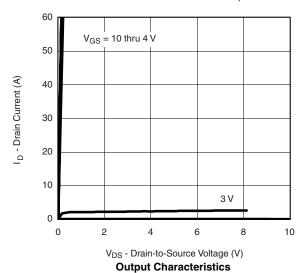
MOSFET SPECIFICATIONS T <sub>J</sub> = 25 °C, unless otherwise noted								
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit		
Static								
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.0		3.0	V		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C			1	μΑ		
					5			
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	30			Α		
Drain-Source On-State Resistance <sup>a</sup>	D	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 25 A		0.0024	0.0030	Ω		
	R <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, I_D = 19 \text{ A}$		0.0031	0.0040			
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 25 A		110		S		
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	I <sub>S</sub> = 2.9 A, V <sub>GS</sub> = 0 V		0.72	1.1	V		
Dynamic <sup>b</sup>								
Input Capacitance	C <sub>iss</sub>			5600				
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		860		pF		
Reverse Transfer Capacitance	C <sub>rss</sub>			415				
Total Gate Charge	$Q_g$			36	50			
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 20 \text{ A}$		18		nC		
Gate-Drain Charge	$Q_{gd}$			10				
Gate Resistance	$R_g$		0.6	1.3	2.0	Ω		
Turn-On Delay Time	t <sub>d(on)</sub>			24	35			
Rise Time t <sub>r</sub>		$t_r$ $V_{DD} = 15 \text{ V}, R_L = 15 \Omega$		16	25			
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D\cong$ 1.0 A, $V_{GEN}$ = 10 V, $R_G$ = 6 $\Omega$		90	140	ns		
Fall Time	t <sub>f</sub>			32	50			
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 2.9 A, di/dt = 100 A/μs		45	70			

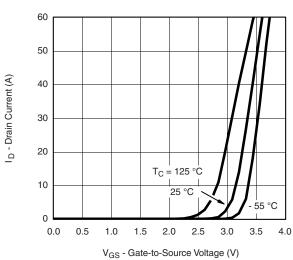
#### Notes:

- a. Pulse test; pulse width  $\leq$  300  $\mu s,$  duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

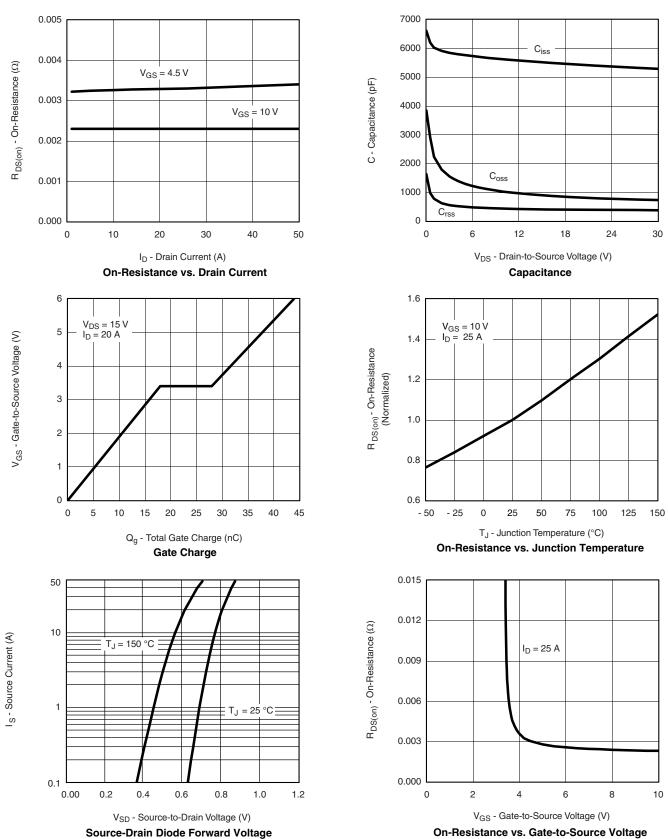




**Transfer Characteristics** 



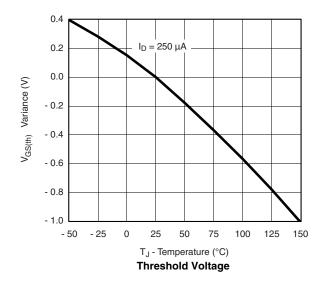
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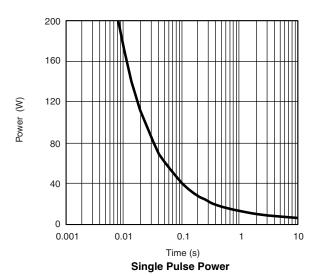


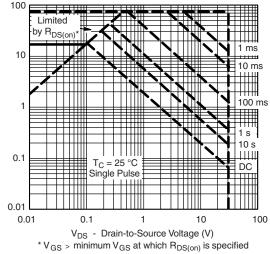
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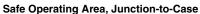
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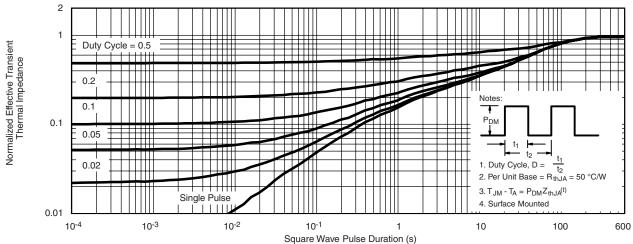
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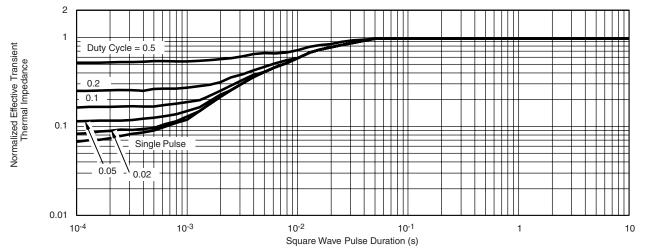




Normalized Thermal Transient Impedance, Junction-to-Ambient



#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="http://www.vishay.com/ppg?73152">http://www.vishay.com/ppg?73152</a>.

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